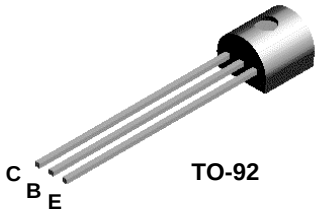
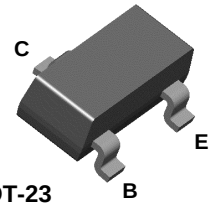
FAIRCHILD
SEMICONDUCTOR TM

2N4124



TO-92

MMBT4124



SOT-23
Mark: ZC

NPN General Purpose Amplifier

This device is designed as a general purpose amplifier and switch. The useful dynamic range extends to 100 mA as a switch and to 100 MHz as an amplifier.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	25	V
V_{CBO}	Collector-Base Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	200	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N4124	*MMBT4124	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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NPN General Purpose Amplifier
(continued)

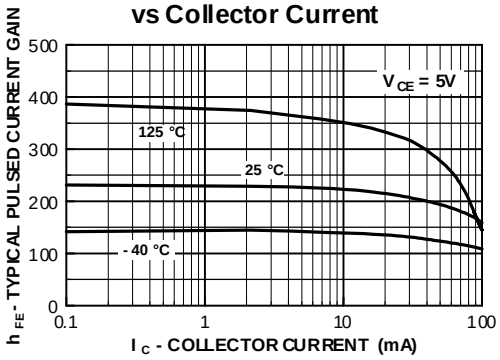
Electrical Characteristics
TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C = 1.0 mA, I_B = 0	25		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 10 µA, I_E = 0	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_C = 10 µA, I_C = 0	5.0		V
I_{CBO}	Collector Cutoff Current	V_{CB} = 20 V, I_E = 0		50	nA
I_{EBO}	Emitter Cutoff Current	V_{EB} = 3.0 V, I_C = 0		50	nA
ON CHARACTERISTICS*					
h_{FE}	DC Current Gain	I_C = 2.0 mA, V_{CE} = 1.0 V I_C = 50 mA, V_{CE} = 1.0 V	120 60	360	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 50 mA, I_B = 5.0 mA		0.3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 50 mA, I_B = 5.0 mA		0.95	V
SMALL SIGNAL CHARACTERISTICS					
f_T	Current Gain - Bandwidth Product	I_C = 10 mA, V_{CE} = 20 V, f = 100 MHz	300		MHz
C_{obo}	Output Capacitance	V_{CB} = 5.0 V, I_E = 0, f = 100 kHz		4.0	pF
C_{ibo}	Input Capacitance	V_{BE} = 0.5 V, I_C = 0, f = 1.0 kHz		8.0	pF
C_{cb}	Collector-Base Capcitance	V_{CB} = 5.0 V, I_E = 0, f = 100 kHz		4.0	pF
h_{fe}	Small-Signal Current Gain	V_{CE} = 10 V, I_C = 2.0 mA, f = 1.0 kHz	120	480	
NF	Noise Figure	I_C = 100 µA, V_{CE} = 5.0 V, R_S =1.0kΩ, f=10 Hz to 15.7 kHz		5.0	dB

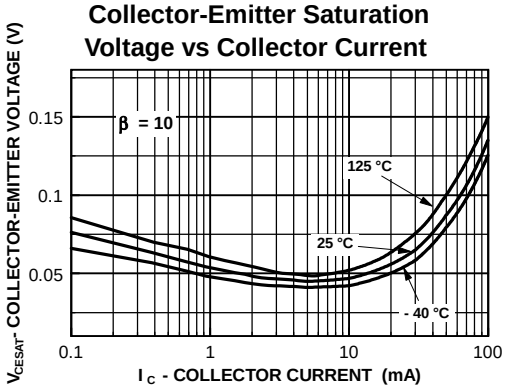
*Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%

Typical Characteristics

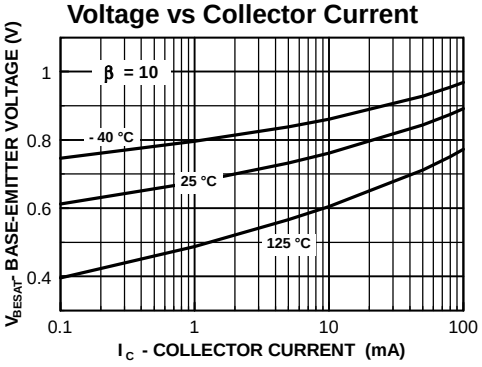
Typical Pulsed Current Gain vs Collector Current



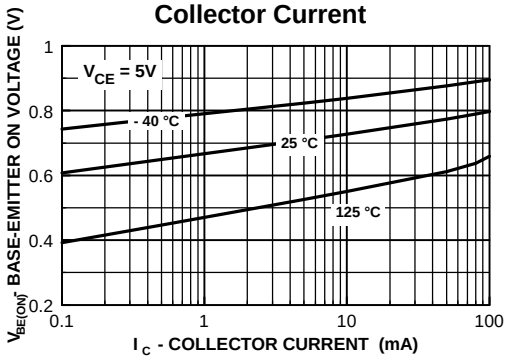
Collector-Emitter Saturation Voltage vs Collector Current



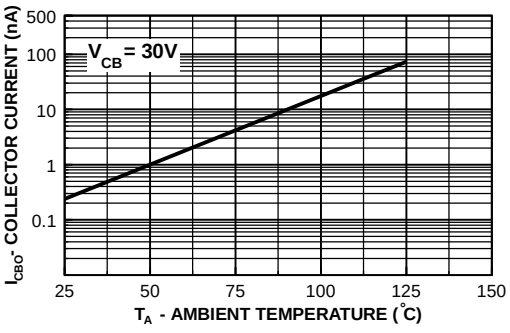
Base-Emitter Saturation Voltage vs Collector Current



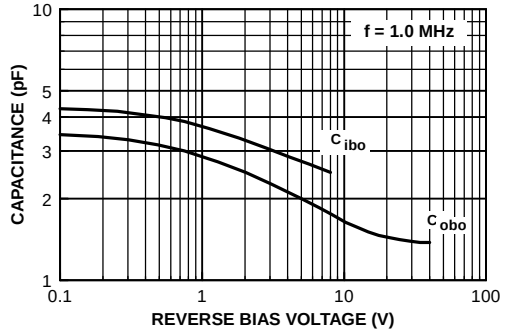
Base-Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature

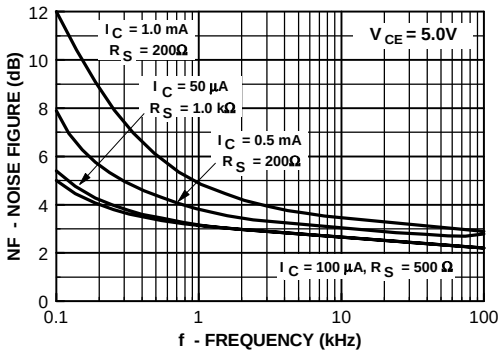


Capacitance vs Reverse Bias Voltage

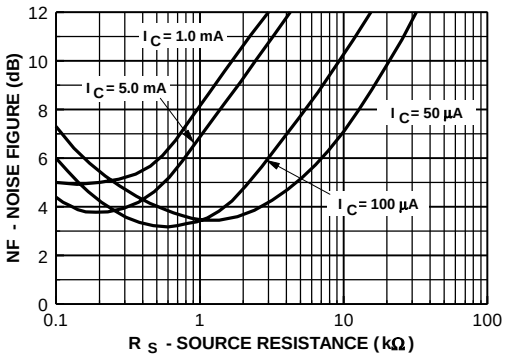


Typical Characteristics (continued)

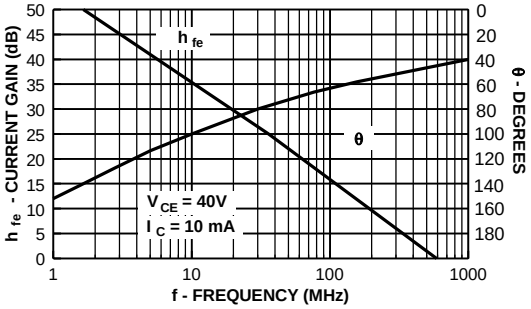
Noise Figure vs Frequency



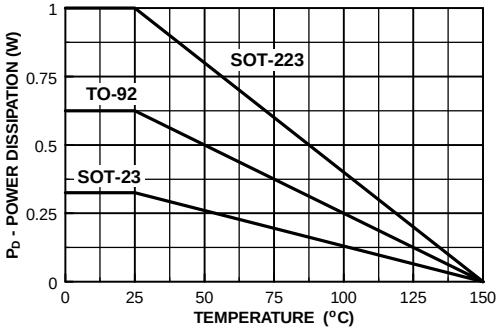
Noise Figure vs Source Resistance



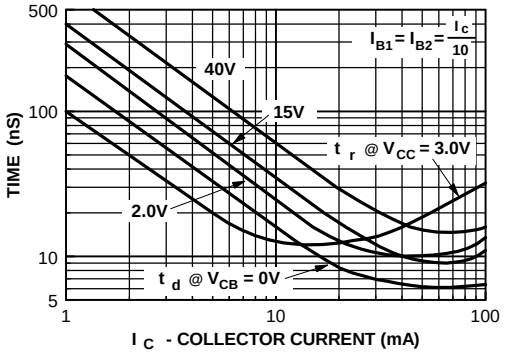
Current Gain and Phase Angle vs Frequency



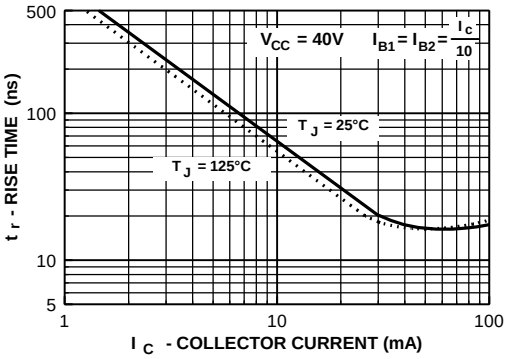
Power Dissipation vs Ambient Temperature



Turn-On Time vs Collector Current

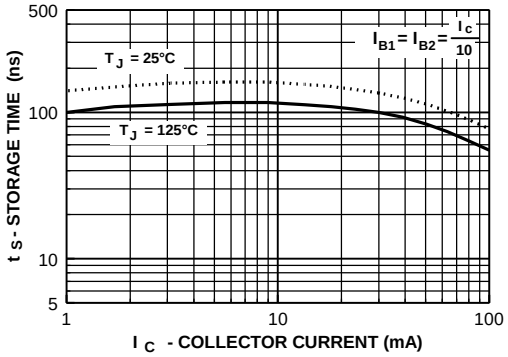


Rise Time vs Collector Current

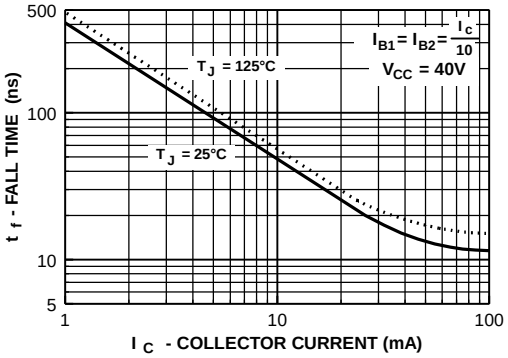


Typical Characteristics (continued)

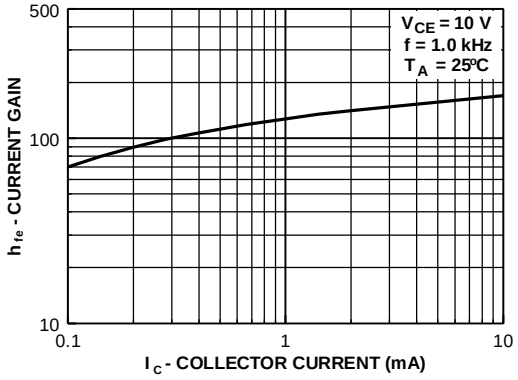
Storage Time vs Collector Current



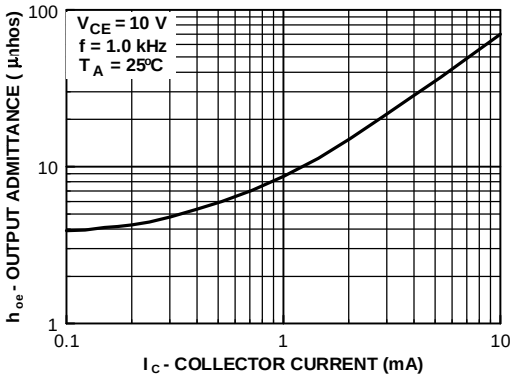
Fall Time vs Collector Current



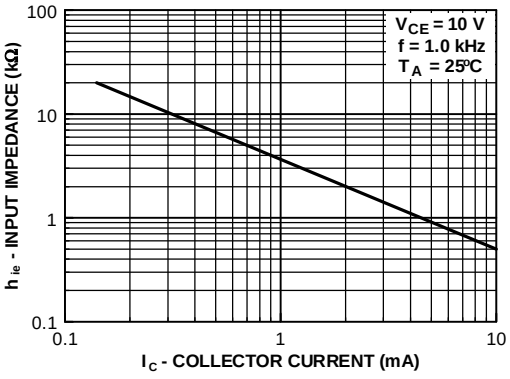
Current Gain



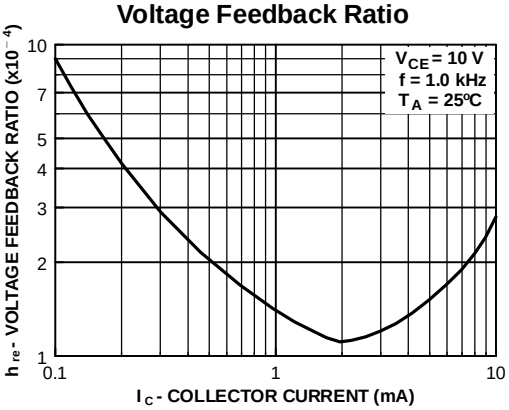
Output Admittance



Input Impedance



Voltage Feedback Ratio



NPN General Purpose Amplifier
(continued)

Test Circuits

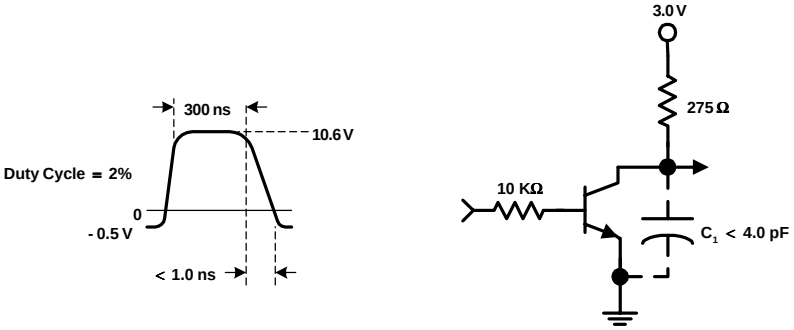


FIGURE 1: Delay and Rise Time Equivalent Test Circuit

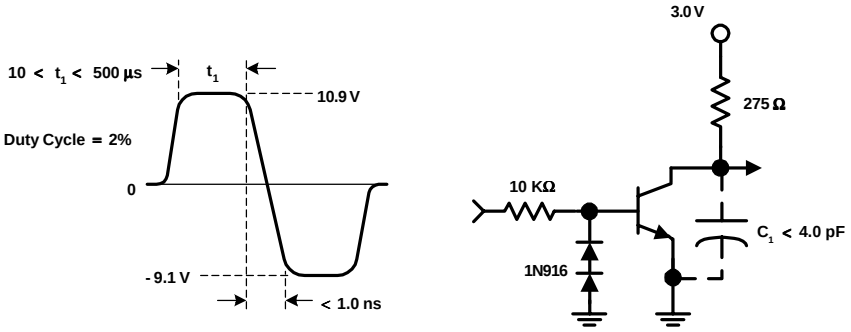


FIGURE 2: Storage and Fall Time Equivalent Test Circuit

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